L Number	Hits	Search Text	USPAT	Time stamp 2002/10/21 14:40
- ;	1	"5604059".PN.	EPO;	2002/10/21 16:19
_ ;	1	430/311-313,394.ccls. and (interlac\$ or	DERWENT;	2002,10,21
:	•	intertwin\$ or double adj expos\$)	IBM TDB	
4	i	1 (interplace or	USPAT;	2002/11/21 13:09
. ;	146	430/311-313,394.ccls. and (interlac\$ or	US-PGPUB;	2002, 22, 02
i		intertwin\$ or double adj expos\$)	JPO	
ì			USPAT	2002/10/21 18:09
	1	"6042998". PN.	USPAT	2002/10/21 18:13
-		"5989952". PN.	USPAT	2002/10/21 18:15
- !	_	"5841143".PN.	USPAT;	2002/12/04 09:54
-	4951	430/311-313,394.ccls.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	!		IBM TDB	
		(photoresist or resist or photopolymer\$7)	USPAT;	2002/11/21 13:23
-	1481	and (etch or etched or etching or etchant)	US-PGPUB;	
		and (etch or etched of etching of etchant) and ((doubl\$3 or plural\$4) same expos\$)	EPO; JPO;	
		same (perpendicular\$3 or cross\$3 or	IBM TDB	
	i	same (perpendiculary) of Clossys of interlac\$3 or intertwin\$3)		
		((photoresist or resist or photopolymer\$7)	USPAT;	2002/11/21 13:55
-	698	and (etch or etched or etching or etchant)	US-PGPUB;	i
		and ((doubl\$3 or plural\$4) same expos\$)	EPO; JPO;	
		same (perpendicular\$3 or cross\$3 or	IBM TDB	
		interlac\$3 or intertwin\$3)) and		
		interlacts or intercumnss/ and semiconduct\$3 and (stor\$3 or capacit\$4)		1
		semiconducts and (Stores of Capacity)	USPAT;	2002/11/21 13:56
-	541	(((photoresist or resist or	US-PGPUB;	
		photopolymer\$7) and (etch or etched or etching or etchant) and ((doub1\$3 or	EPO; JPO;	
		plural\$4) same expos\$) same	IBM TDB	
	1	(perpendicular\$3 or cross\$3 or interlac\$3	_	
		or intertwin\$3)) and semiconduct\$3 and		
	ļ	(stor\$3 or capacit\$4)) and ((line\$2 or		
		parallel) same expos\$3)		
	1	1	USPAT;	2002/11/21 13:56
_	398	photopolymer\$7) and (etch or etched or	US-PGPUB;	
		etching or etchant) and ((doubl\$3 or	EPO; JPO;	
	1	plural\$4) same expos\$) same	IBM_TDB	-
		(perpendicular\$3 or cross\$3 or interlac\$3	_	1
		or intertwin\$3)) and semiconduct\$3 and		
		(stor\$3 or capacit\$4)) and ((line\$2 or		
		parallel) same expos\$3)) and develop\$4		
			USPAT;	2002/11/21 13:57
-	66	photopolymer\$7) and (etch or etched or	US-PGPUB;	
		etching or etchant) and ((doubl\$3 or	EPO; JPO;	
	į	nlural\$4) same expos\$) same	IBM_TDB	
		(perpendicular\$3 or cross\$3 or interlac\$3		Į.
		or intertwin\$3)) and semiconduct\$3 and		
	ĺ	(stors3 or capacit\$4)) and ((line\$2 or	į	
İ		narallel) same expos\$3)) and develop\$4)		
	İ	and (dynamic adj random adj access or		
		DAM)		1000 (11 (01 13.5)
	769	((photoresist or resist or photopolymer\$/)	USPAT;	2002/11/21 13:5
_	/ / /	and letch or etched or etching or etchant,	102-101001	
	Ì	and ((doubl\$3 or plural\$4) same expos\$)	EFO, OLO,	
ļ		same (perpendicular\$3 or cross\$3 or	IBM_TDB	
		intorlack3 or intertwin\$3)) and		
		semiconduct\$3 and (stor\$3 or capacit\$4 or		
	Į	memor\$5)		0000/11/01 13 5
	602	///photoresist or resist or	USPAT;	2002/11/21 13:5
-	, 602	photopolymer\$7) and (etch or etched or	US-PGPUB;	
	1	etching or etchant) and ((doubl\$3 or	EPO; JPO;	1
	+	Talurals/) same exposs) same	IBM_TDB	
		(nerpendicular\$3 or cross\$3 or interlac\$3		
		or intertwin\$3)) and semiconduct\$3 and		
		(stors3 or capacit\$4 or memor\$5)) and		
ł		((line\$2 or parallel) same expos\$3)		

			USPAT;	2002/11/21 13:57
1	438	((((photoresist or resist or photopolymer\$7) and (etch or etched or	US-PGPUB;	!
ļ	l	etching or etchant) and ((doubl\$3 or	EPO; JPO;	
İ	1	-1	IBM_TDB	
İ	Ì	/normandicular\$3 or cross\$3 or interiocy3		
1		intortwin(3)) and semiconducted and		
		(-tc3 or capacits4 or memorab)) and		
i		((line\$2 or parallel) same expos\$3)) and		
		develop\$4		2002/11/22 11:52
	74	////photoresist or resist or	USPAT;	2002/11/22 11:32
	/4	-betopolymer\$7) and (etch of etched of	US-PGPUB;	
,		etching or etchant) and ((doubles of	EPO; JPO;	
		- 1641 camo evposS) same	IBM_TDB	
1		V		
i		l		
		l, barca or capacits4 or memorable did		
		1 //linger or parallel) same exposisi/ and		
1		develop\$4) and (dynamic adj random da)		
		laccess or DRAM)	USPAT;	2002/11/22 11:55
	331	1,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	US-PGPUB;	
		-betonolymer\$7) and (etch of etched of	EPO; JPO;	
•		letching or etchant) and ((doubly) of	IBM TDB	
i		1 1 1041 como evpossi same	1011_100	
1		Transpliculars or crosss or interfaces		
		i =====tring3 or row or column)) and		
1		1 duates and (stors) of Capacity of	1	1
		I and (lines) or baldiel same		
ļ		Tampage 1 and developed and (dynamic ad)		
		random adj access or DRAM or memory)	USPAT:	2002/11/22 13:35
.	62	((((((photoresist or resist or	US-PGPUB;	
		photopolymer\$7) and (etch or etched or	EPO; JPO;	
		etching or etchant) and ((doubl\$3 or	IBM TDB	
- 5		plural\$4) same expos\$) same	_	1
		(perpendicular\$3 or cross\$3 or interlac\$3	1	1
		or intertwin\$3 or row or column)) and	ŧ	
		or intertwints of tem semiconduct\$3 and (stor\$3 or capacit\$4 or semiconduct\$3 and (stor\$3 or parallel) same	1	1
		memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj		
		expos(3)) and develop(4) and (amory)) and random adj access or DRAM or memory)) and		
		random adj access of bloar of memory with ((round\$3 with corner) or (optical with		
		((round\$3 with corner) or (options) proximity) or (line with short\$5))		100000
	1		USPAT;	2002/11/22 12:30
_	4	photopolymer\$7) and (etch or etched or	US-PGPUB;	
		etching or etchant) and ((doubl\$3 or	EPO; JPO;	
		1 - 1041 camo evposs) same	IBM_TDB	
		/		
	1	intertines or row or column) and		
		I amb monducted and (stored of Capacity of	1	
		and ((lines) or paratter) same		
		- coll and develops 4) and (dylianic ad)		
	1	and access or DRAM or memory), and		
		1 / dea with corner) or (ODtical With		
		proximity) or (line with short\$5))) and		
		1,20/312 ccls		2002/11/22 12:3
		al /////nhotoresist or resist or	USPAT;	2002/11/22 12.3
-	1	1 - b - b coolimars7) and (etch of etched of	US-PGPUB;	
		etching or etchant) and ((doubl\$3 or	EPO; JPO;	
		1 - 1041 OVDOSSI SAMP	IBM_TDB	
	ŀ	1 contact of the cont		
		the second of th		
		CEII and [[IIDE5] OF Datailer] Sums	1	
	1	the case and develops all and (dyliamic ad)	! !	
	i .	random adj access or DRAM or memory)) and	1 +	4 ·
	Ī	1 mandom add access of bight of more		
х.		1 // on dea with corner) or (optical with		
		((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and		

			USPAT;	2002/11/22 13:11
Γ -	-	3 (((((((photoresist or resist or	US-PGPUB;	
	1	photopolymer\$7) and (etch or etched or		i
	r	etching or etchant) and ((doub1\$3 or	EPO; JPO;	[
		nlurals4) same expos5) same	IBM_TDB	1
	1	(perpendicular\$3 or cross\$3 or interlac\$3	1	!
	i	or intertwin\$3 or row or column)) and	1	1
		semiconduct\$3 and (stor\$3 or capacit\$4 or		1
	1	semiconductos and (storos or parallel) same		
	1	memor\$5)) and ((line\$2 or parallel) same		
	1	expos\$3)) and develop\$4) and (dynamic adj		1
	į	random adj access or DRAM or memory)) and		1
		((round\$3 with corner) or (optical with	1	
i	l	proximity) or (line with short\$5))) and	1	
	i	430/313.ccls.		2002/11/22 13:11
	i	3 / ///// (photoresist or resist or	USPAT;	2002/11/22 13:11
-		photopolymer\$7) and (etch or etched or	US-PGPUB;	
		etching or etchant) and ((doubl\$3 or	EPO; JPO;	
		plural\$4) same expos\$) same	IBM_TDB	1
		(perpendicular\$3 or cross\$3 or interlac\$3	_	
	i	(perpendiculars) of crosses of income		
1	1	or intertwin\$3 or row or column)) and		
	1	semiconduct\$3 and (stor\$3 or capacit\$4 or		1
		memor\$5)) and ((line\$2 or parallel) same		
[ovposs3)) and develop\$4) and (dynamic adj		
		random adi access or DRAM or memory)) and		
	1	//rounds3 with corner) or (optical with		
	1	proximity) or (line with short\$5))) and		
	1	430/311.ccls.		
[_i	1430/311.0010.		

			ucpam.	2002/12/04 09:57
-	57	<pre>((((((photoresist or resist or photopolymer\$7) and (etch or etched or</pre>	USPAT; US-PGPUB;	2002/12/04 09:57
ı	i	etching or etchant) and ((doubl\$3 or	EPO; JPO;	
i		plural\$4) same expos\$) same	IBM_TDB	'.
;	i	(perpendicular\$3 or cross\$3 or interlac\$3	_	
1	ŀ	or intertwin\$3 or row or column)) and		
•	ŀ	semiconduct\$3 and (stor\$3 or capacit\$4 or		
		memor\$5)) and ((line\$2 or parallel) same		
	1	expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and		
1		((round\$3 with corner) or (optical with		
		proximity) or (line with short\$5)) not		
	i i	((((((((photoresist or resist or		
		photopolymer\$7) and (etch or etched or		
	†	etching or etchant) and ((doub1\$3 or		
		plural\$4) same expos\$) same		
		(perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and		
		semiconduct\$3 and (stor\$3 or capacit\$4 or		
		memor\$5)) and ((line\$2 or parallel) same		
		expos\$3)) and develop\$4) and (dynamic adj		
İ		random adj access or DRAM or memory)) and		
		((round\$3 with corner) or (optical with		
		proximity) or (line with short\$5))) and		
		430/312.ccls.) not (((((((photoresist or		
	ļ	resist or photopolymer\$7) and (etch or etched or etching or etchant) and		
		((doubl\$3 or plural\$4) same expos\$) same		
	1	(perpendicular\$3 or cross\$3 or interlac\$3		
	Ì	or intertwin\$3 or row or column)) and		
		semiconduct\$3 and (stor\$3 or capacit\$4 or		
		memor\$5)) and ((line\$2 or parallel) same		
		expos\$3)) and develop\$4) and (dynamic adj		
		random adj access or DRAM or memory)) and		
		((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and		
		430/394.ccls.) not (((((((photoresist or	Ì	
		resist or photopolymer\$7) and (etch or		
		etched or etching or etchant) and		
		((doub1\$3 or plural\$4) same expos\$) same		
		(perpendicular\$3 or cross\$3 or interlac\$3		
		or intertwin\$3 or row or column)) and		
		<pre>semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same</pre>		
		expos\$3)) and develop\$4) and (dynamic adj		
		random adj access or DRAM or memory)) and		
		((round\$3 with corner) or (optical with		
		proximity) or (line with short\$5))) and		
		430/313.ccls.) not (((((((photoresist or		
		resist or photopolymer\$7) and (etch or		
		etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same		
		(doubles of piurals4) same expose, same (perpendicular\$3 or cross\$3 or interlac\$3	1	
	:	or intertwin\$3 or row or column)) and		
		semiconduct\$3 and (stor\$3 or capacit\$4 or		
		memor\$5)) and ((line\$2 or parallel) same		
		expos\$3)) and develop\$4) and (dynamic adj		
		random adj access or DRAM or memory)) and		
		((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and		
		proximity) or (line with shorts);;; and 430/311.ccls.)		. 01
_	5004	430/311-313,394.ccls.	USPAT;	2002/12/04 10:24
_	2003	,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/12/04 10:27
-	2009	430/312,394.ccls.	USPAT; US-PGPUB;	2002/12/04 10.2/
			EPO; JPO;	
			DERWENT;	
		i e e e e e e e e e e e e e e e e e e e	IBM TDB	1

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-	324	430/312,394.cor.	USPAT;	2002/12/04 15:45
	i 1		US-PGPUB;	
			EPO; JPO;	i
			DERWENT;	1
			IBM_TDB	
-	13		USPAT	2002/12/04 12:36
1	1	"5340700" "5424154" "5532090"		
		"5563012" "5620816" "5702868"		
	:	"5804339" "5807649" "5851707"]
		"5863677").PN.	HCDAM.	2002/12/06 13:59
-	1685	430/312,394.ccls. not 430/312,394.cor.	USPAT;	2002/12/06 13:39
	1		US-PGPUB; EPO; JPO;	
	i		DERWENT;	
	1		IBM TDB	
	2995	430/311-313,394.ccls. not	USPAT;	2002/12/04 19:14
-	2993	430/312,394.ccls. not 430/312,394.cor.	US-PGPUB;	
		130/312/331.00281 100/012/0711001	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	(("5103274") or ("5120671")).PN.	USPAT;	2002/12/07 14:02
			US-PGPUB	
_	3	(("6184151") or ("5955244") or	USPAT;	2002/12/10 14:44
		("20010028422")).PN.	US-PGPUB	